



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-323 Plastic-Encapsulate Diode

CMSD2004S

SWITCHING DIODE

FEATURES

Power dissipation

P_D : 250 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_F : 225 mA

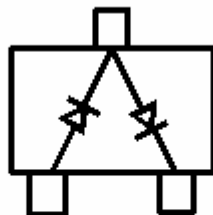
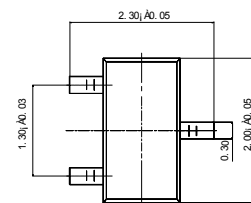
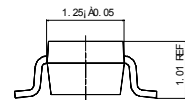
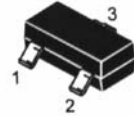
Collector-base voltage

V_R : 240 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-323



Marking: B6D

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	240		V
Reverse voltage leakage current	I_R	$V_R=240V$		0.1	μA
Forward voltage	V_F	$I_F=100mA$		1	V
Diode capacitance	C_D	$V_R=0V, f=1MHz$		5	pF
Reveres recovery time	t_{rr}	$I_F=I_R=30mA, R_L=100\Omega$		50	ns